Large Diameter M-HEMT & InP-HEMT Epiwafers Grown in Multicharge MOVPE Reactors

*Takeshi Tanaka, Tatsushi Hashimoto, Mineo Washima and **Yohei Otoki
Advanced Research Center (ARC), Hitachi Cable, Ltd., 3550 Kidamari, Tsuchiura, Ibaraki, 300-0026 Japan
phone: +81-298-26-7655, fax: +81-298-26-6411, email: ttanaka@arc.hitachi-cable.co.jp

Abstract

Large diameter M-HEMT and InP-HEMT epitaxial wafers were fabricated in a lately installed Hitachi Cable’s MOVPE reactor that was outfitted with mass production capability (8x4” or 5x6”). M-HEMT structure was combined with In$_{0.15}$Ga$_{0.85}$P layer, which had the same lattice constant with In$_{0.36}$Ga$_{0.64}$As channel and could be used for etch stop and/or surface passivation. Both of the M-HEMT and InP-HEMT wafers showed reasonable performance with abrupt etching selectivity, which will simplify device fabrication processed and realize high yield rates. Excellent uniformity overall the substrates was also achieved by optimizing atmospheres inside the reactor. These wafers will satisfy the demands in the next generation low noise and high power RF devices for wireless application and opto-electronic communication markets.

INTRODUCTION

The expansion of cellular phone market and upcoming demand in millimeter-wave operations in wireless-LAN, LMDS and ITS have stimulated the recent development of M(Metamorphic)-HEMT, which has the right characteristics for low noise and high power amplification at high frequency. Meanwhile, “wired” fiber-related components, in which 40Gbit/sec optic communication will be started in 2001, needs digital and analog integrated circuit with high maximum oscillation frequency. InP-HEMT and M-HEMT, which have high electron mobility and enough transport characteristics, are also indispensable devices for these high-speed ICs. Thus there is an impending need of large diameter epiwafers of M-HEMT and InP-HEMT, especially wafers grown by MOVPE (Metal Organic Vapor Phase Epitaxy), which has some advantages over the other epitaxial systems from the viewpoint of commercial application. At last year’s MANTECH conference, we made the first report on the feasibility of M-HEMT wafers using MOVPE method [1]. Our client's requests motivate us to transfer this laboratory level experimental technique into mass production technology. In this report, we will show successful development of the latest diameter M-HEMT wafer growth using Hitachi-Cable’s lately installed multi-charge MOVPE reactor. The possibility of InGaP layer growth, which lattice matches to M-HEMT channel and will be used as etch stopper, is also explained. In addition, our capability of fabricating high uniformity InP-HEMT epiwafer, which is the precedent alternative of M-HEMT, will be shown.

MANUFACTURING EQUIPMENT

We installed a new MOVPE system which has been designed to minimize the total epigrowth time and increase the number of holding wafers while maintaining clean surfaces, a contamination free epi/substrate interface, high doping efficiency, excellent uniformity and reproducibility reported before[2]. The planetary configuration and the face-down system were combined to improve throughput and realize these quality (Fig.1). The wafers, five 6” or eight 4”, are loaded automatically from cassette to the reactor and set in a face down style. Gas then flows from the center of the bottom plate of the reactor. Both the susceptor (wafer holder) and the individual wafer rotate during the growth to achieve inside-wafer and wafer-to-wafer uniformity. The heating and cooling time are much reduced compared to the conventional horizontal-flow type reactor.
PH3 gases were chosen as group V sources. n-type doping is achieved by selenium, using H2Se as a precursor. We need relatively high substrate temperature up to 700°C, in order to prevent impurity contamination into the InAlAs layer and accomplish superior morphology of the surfaces of epiwafers. Carrier gas flow rate and susceptor heater balance were optimized to achieve uniformity of indium composition in the epilayers. Figure 2 shows the cross sectional view of one of the M-HEMT epi structures grown on S.I. GaAs (100) substrate. The indium composition in each layer was determined by using 4-crystal XRD. Step-graded InAlAs buffer layers effectively decrease misfit dislocations and In0.35Al0.65As (indium mole fraction x=35-40%) channel layer will show high mobility, high sheet electron concentration and relatively high on-state breakdown voltages. In addition, an In0.9Ga0.1P (indium mole fraction y=85-90%) etch-stop and passivation layer was inserted upon the InAlAs shortkly layer. The phosphide layer has high etching selectivity, which can make device processing more simple, improve Vp uniformity and realize high yield rates. It is also expected that phosphide surface passivation layer leads to better noise performance and long-term reliability. In order to evaluate the ability to etch-stop, we grew a wafer with n-In0.36Ga0.64As(200nm)/i-In0.85Ga0.15P(10nm)/n-In0.36Ga0.64As(200nm) epitaxial structure. This sample was etched by H3PO4:H2O2:DI water=1:1:10 solution and the change of sheet carrier concentration in this sample along with the etching time was plotted to calculated the etch rate and etching selectivity between the arsenide and phosphide layers. InP-HEMT, which also has InAlAs buffer/shottky and InGaAs channel layers, although the indium composition is higher (53%) than M-HEMT, was also grown on 4” semi-insulating M/A-COM InP(100) substrate, using the same growth condition with our M-HEMT. Electron mobility in both of M-HEMT and InP-HEMT were characterized by Van der Pauw measurement at room temperature.

**RESULTS AND DISCUSSION**

The dispersion of electron mobility in the 4-inch M-HEMT epiwafers are plotted in figure 3. The mobility in conventional P-HEMT was also added in the figure for comparison. M-HEMT wafer showed 8,000 cm²/Vs mobility at 2.5x10¹² cm⁻² sheet carrier concentration, which was about 30% overtaking the mobility in P-HEMT epiwafer. The higher indium composition in InGaAs channel layer grown on step-graded InAlAs buffer layer in metamorphic epi structure realized this high electron transportation characteristic. Variation of the mobility in M-HEMT was 1.48%, meaning that high electron mobility was uniformly achieved over all 4-inch GaAs substrate. The mobility in InP-HEMT was also shown in figure 3. The value reached to 12,000 cm²/Vs at room temperature and its diagonal uniformity was also sufficient.

Figure 4 shows the result of etch-stop characterization. In0.35Ga0.64As layer was etch during the first 30 second at etch rate of 6.7 nm/sec, and then InGaP layer appeared to surface, where etch rate was reduced to 0.167 nm/sec. It is understood that etch speed was abruptly changed at the InGaAs/InGaP interface and enough etching selectivity was obtained. The growth of phosphide layers with abrupt interfaces is one of our

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<td>All samples were grown in MOVPE system mentioned above.</td>
<td>Atmosphere in the reactor is low pressure (50 Torr)</td>
<td>Hydrogen. Trimethylindium (TMI), trimethylaluminum (TMA) and trimethylgallium (TMG) were used as group III elements precursors, and both of arsine (AsH3) and phosphine (PH3) gases were chosen as group V sources. n-type doping is achieved by selenium, using H2Se as a precursor. We need relatively high substrate temperature up to 700°C, in order to prevent impurity contamination into the InAlAs layer.</td>
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![Figure 2 Cross section of the structure of M-HEMT epiwafer used in this study.](image)

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greatest assets with MOVPE, compared with solid source MBE that has difficulty in phosphide epi growth.

CONCLUSIONS

We are now ready to supply M-HEMT epiwafer with InGaP etch-stop & passivation layer and InP-HEMT epiwafer by using our new multicharge high throughput MOVPE reactor in mass production line. Both of 4 inch M-HEMT and InP-HEMT wafers showed reasonable electric characteristics and excellent uniformity. These wafers will satisfactorily meet the demands in the next generation low noise and power RF devices for wireless application markets.

REFERENCES